



Insulated Gate Bipolar Transistors (IGBT)

ECG Type	Description	Collector to Emitter Voltage V _{CES}	DC Collector Current I _C Amps	Gate to Emitter Voltage V _{GES}	Gate to Emitter Cutoff Voltage V _{GE (th)}	Collector to Emitter Saturation Voltage V _{CE (sat)}	Input Cap C _{IES} pf	Device Dissipation @ T _c =25°C P _D Watts	Package	
									Case/Fig/Basing	
ECG3300 ▲	IGBT, N-Ch, Enhancement	400	10	±25	7	8	1350	30	TO-220J Fig. T41-1 	
					td(off)=7 μs, td(on)=0.5 μs, tf=6 μs, tr=0.5 μs					
ECG3301 ▲	IGBT, N-Ch, Enhancement	400	15	±25	7	8	2000	40		
					td(off)=7 μs, td(on)=0.5 μs, tf=6 μs, tr=0.5 μs					
ECG3302 ▲	IGBT, N-Ch, Enhancement	600	8	±20	6	4	650	30		
					td(off)=1 μs, td(on)=0.8 μs, tf=.35 μs, tr=0.6 μs					
ECG3303 ▲	IGBT, N-Ch, Enhancement	600	15	±20	6	4	1100	35		
					td(off)=1 μs, td(on)=0.8 μs, tf=.35 μs, tr=0.6 μs					
ECG3310 ▲	IGBT, N-Ch, Enhancement	600	15	±20	6	4	1100	100		TO-3PJ Fig. T48-1 
					td(off)=1 μs, td(on)=0.8 μs, tf=.35 μs, tr=0.6 μs					
ECG3311 ▲	IGBT, N-Ch, Enhancement	600	25	±20	6	4	1400	150		
					td(off)=1 μs, td(on)=0.8 μs, tf=.35 μs, tr=0.6 μs					
ECG3312 ▲	IGBT, N-Ch, Enhancement	1200	8	±20	6	4	1150	100	Collector to Heat Sink	
					td(off)=1.5 μs, td(on)=0.8 μs, tf=0.5 μs, tr=0.6 μs					
ECG3320 ▲	IGBT, N-Ch, Enhancement	600	50	±20	6	4	3500	200		
					td(off)=1 μs, td(on)=0.8 μs, tf=0.35 μs, tr=0.6 μs					
ECG3321 ▲	IGBT, N-Ch, Enhancement	600	80	±20	6	3.5	5500	200		
					td(off)=1 μs, td(on)=0.8 μs, tf=0.4 μs, tr=0.6 μs					
ECG3322 ▲	IGBT, N-Ch, Enhancement	900	60	±25	6	4	5500	200		
					td(off)=1.3 μs, td(on)=0.8 μs, tf=0.4 μs, tr=0.6 μs					
ECG3323 ▲	IGBT, N-Ch, Enhancement	1200	25	±20	6	4	3200	200	Collector to Heat Sink	
					td(off)=1.5 μs, td(on)=0.8 μs, tf=0.5 μs, tr=0.6 μs					

▲ Refer to MOSFET Handling Precautions Page 1-34

IGBT Diagram

